

WHAT IS CLAIMED IS:

1. A camera comprising: /
a main body;
an eyepiece;
a switching unit;
an image receiver; and
a display having a semiconductor device,
wherein the semiconductor device comprises:
a gate electrode formed over a substrate;
a first insulating layer formed over the gate electrode;
a second insulating layer formed over the first insulating layer;
a semiconductor layer formed over the second insulating layer, the
semiconductor layer having at least a channel region and at least one impurity
region;
an inorganic insulating layer formed over the semiconductor layer, the
inorganic insulating layer being in contact with a portion of the impurity region;
and
an organic insulating layer formed over the inorganic insulating layer,
the organic insulating layer being in contact with another portion of the
impurity region.

2. A camera according to claim 1, wherein the gate electrode
comprises at least one layer comprising a material selected from the group
consisting of tantalum, molybdenum, titanium, chromium and silicon.

3. A camera comprising: /
a main body;
an eyepiece;
a switching unit;
an image receiver; and
a display having a semiconductor device,
wherein the semiconductor device comprises:
a gate electrode formed over a substrate;

a first insulating layer comprising silicon nitride formed over the gate electrode;

a second insulating layer comprising silicon oxide formed over the first insulating layer;

a semiconductor layer formed over the second insulating layer, the semiconductor layer having at least a channel region and at least one impurity region;

an inorganic insulating layer formed over the semiconductor layer, the inorganic insulating layer being in contact with a portion of the impurity region; and

an organic insulating layer formed over the inorganic insulating layer, the organic insulating layer being in contact with another portion of the impurity region.

4. A camera according to claim 3, wherein the gate electrode comprises at least one layer comprising a material selected from the group consisting of tantalum, molybdenum, titanium, chromium and silicon.

5. A camera comprising:

a main body;

an eyepiece;

a switching unit;

an image receiver; and

a display having a semiconductor device,

wherein the semiconductor device comprises:

a gate electrode formed over a substrate;

a first insulating layer formed over the gate electrode, the first insulating layer having a thickness of 10-200nm;

a second insulating layer formed over the first insulating layer, the second insulating layer having a thickness of 50-300nm;

a semiconductor layer formed over the second insulating layer, the semiconductor layer having at least a channel region and at least one impurity region;

an inorganic insulating layer formed over the semiconductor layer, the

inorganic insulating layer being in contact with a portion of the impurity region;
and

an organic insulating layer formed over the inorganic insulating layer,
the organic insulating layer being in contact with another portion of the
impurity region.

6. A camera according to claim 5, wherein the gate electrode
comprises at least one layer comprising a material selected from the group
consisting of tantalum, molybdenum, titanium, chromium and silicon.

7. A camera comprising:

a main body;

an eyepiece;

a switching unit;

an image receiver; and

a display having a semiconductor device,

wherein the semiconductor device comprises:

a gate electrode formed over a substrate;

a first insulating layer formed over the gate electrode;

a second insulating layer formed over the first insulating layer;

a semiconductor layer formed over the second insulating layer, the
semiconductor layer having at least a channel region and at least one impurity
region;

an inorganic insulating layer comprising silicon oxide formed over the
semiconductor layer, the inorganic insulating layer being in contact with a
portion of the impurity region; and

an organic insulating layer formed over the inorganic insulating layer,
the organic insulating layer being in contact with another portion of the
impurity region.

8. A camera according to claim 7, wherein the gate electrode
comprises at least one layer comprising a material selected from the group
consisting of tantalum, molybdenum, titanium, chromium and silicon.

9. A camera comprising:
a main body;
an eyepiece;
a switching unit;
an image receiver; and
a display having a semiconductor device,
wherein the semiconductor device comprises:
at least two gate electrodes formed over a substrate;
a first insulating layer formed over the gate electrodes;
a second insulating layer formed over the first insulating layer;
a semiconductor layer formed over the second insulating layer, the
semiconductor layer having at least a channel region and at least one impurity
region;
an inorganic insulating layer formed over the semiconductor layer, the
inorganic insulating layer being in contact with a portion of the impurity region;
and
an organic insulating layer formed over the inorganic insulating layer,
the organic insulating layer being in contact with another portion of the
impurity region.

10. A camera according to claim 9, wherein each of the gate
electrodes comprises at least one layer comprising a material selected from
the group consisting of tantalum, molybdenum, titanium, chromium and
silicon.

11. A camera comprising:
a main body;
an eyepiece;
a switching unit;
an image receiver; and
a display having a driving circuit and a pixel circuit,
wherein a plurality of thin film transistors formed in the pixel circuit,
each of the thin film transistors comprising:
a gate electrode formed over a substrate;

a first insulating layer formed over the gate electrode;
a second insulating layer formed over the first insulating layer;
a semiconductor layer formed over the second insulating layer, the semiconductor layer having at least a channel region and at least one impurity region;
an inorganic insulating layer formed over the semiconductor layer, the inorganic insulating layer being in contact with a portion of the impurity region;
and
an organic insulating layer formed over the inorganic insulating layer, the organic insulating layer being in contact with another portion of the impurity region.

12. A camera according to claim 11, wherein the gate electrode comprises at least one layer comprising a material selected from the group consisting of tantalum, molybdenum, titanium, chromium and silicon.

13. A semiconductor device comprising:
a gate electrode formed over a substrate;
a first insulating layer formed over the gate electrode;
a second insulating layer formed over the first insulating layer;
at least a channel region and an impurity region formed over the second insulating layer;
an inorganic insulating layer formed over the channel region and the impurity region, the inorganic insulating layer being in contact with a portion of the impurity region; and
an organic insulating layer formed over the inorganic insulating layer, the organic insulating layer being in contact with another portion of the impurity region.

14. A semiconductor device according to claim 13, wherein the gate electrode comprises at least one layer comprising a material selected from the group consisting of tantalum, molybdenum, titanium, chromium and silicon.

15. A semiconductor device according to claim 13, wherein the semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle-type display, a player for a recording medium, a digital still camera, a front-type projector and a rear-type projector.

16. A semiconductor device comprising:
a gate electrode formed over a substrate;
a first insulating layer comprising silicon nitride formed over the gate electrode;
a second insulating layer comprising silicon oxide formed over the first insulating layer;
at least a channel region and an impurity region formed over the second insulating layer;
an inorganic insulating layer formed over the channel region and the impurity region, the inorganic insulating layer being in contact with a portion of the impurity region; and
an organic insulating layer formed over the inorganic insulating layer, the organic insulating layer being in contact with another portion of the impurity region.

17. A semiconductor device according to claim 16, wherein the gate electrode comprises at least one layer comprising a material selected from the group consisting of tantalum, molybdenum, titanium, chromium and silicon.

18. A semiconductor device according to claim 16, wherein the semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle-type display, a player for a recording medium, a digital still camera, a front-type projector and a rear-type projector.

19. A semiconductor device comprising:
a gate electrode formed over a substrate;
a first insulating layer formed over the gate electrode, the first

insulating layer having a thickness of 10-200nm;

a second insulating layer formed over the first insulating layer, the second insulating layer having a thickness of 50-300nm;

a channel region and an impurity regions formed over the second insulating layer;

an inorganic insulating layer formed over the channel region and the impurity region, the inorganic insulating layer being in contact with a portion of the impurity region; and

an organic insulating layer formed over the inorganic insulating layer, the organic insulating layer being in contact with another portion of the impurity region.

20. A semiconductor device according to claim 19, wherein the gate electrode comprises at least one layer comprising a material selected from the group consisting of tantalum, molybdenum, titanium, chromium and silicon.

21. A semiconductor device according to claim 19, wherein the semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle-type display, a player for a recording medium, a digital still camera, a front-type projector and a rear-type projector.